

7-01-17

## SILICON RECTIFIER DIODES



Diffused silicon rectifier diodes in DO-4 metal envelopes, intended for power rectifier applications.

The series consists of the following types:

Normal polarity (cathode to stud): BYX42-300 to 1200.

Reverse polarity (anode to stud): BYX42-300R to 1200R.

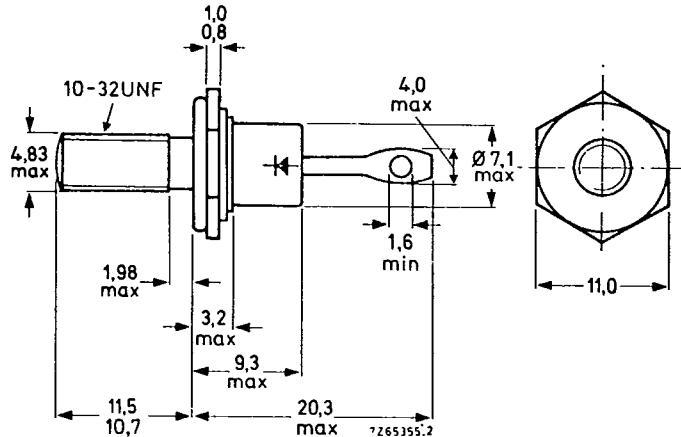
## QUICK REFERENCE DATA

		BYX42-300(R)	600(R)	1200(R)
Repetitive peak reverse voltage	V <sub>RRM</sub>	max. 300	600	1200 V
Average forward current	I <sub>F(AV)</sub>	max. 12		A
Non-repetitive peak forward current	I <sub>FSM</sub>	max. 125		A

## MECHANICAL DATA

Dimensions in mm

DO-4



Net mass: 6 g

Torque on nut: min. 0,9 Nm

(9 kg cm)

Diameter of clearance hole: 5,2 mm

max. 1,7 Nm

(17 kg cm)

Accessories supplied on request:

see ACCESSORIES section

Supplied with device: 1 nut, 1 lock washer

Nut dimensions accross the flats: 9,5 mm

The mark shown applies to normal polarity types.



Products approved to CECC 50 009-020 available on request.

## RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

<u>Voltages</u>		BYX42-300(R)	600(R)	1200(R)	
Non-repetitive peak reverse voltage ( $t \leq 10$ ms)	$V_{RSM}$	max. 300	600	1200	V
Repetitive peak reverse voltage ( $\delta \leq 0,01$ )	$V_{RRM}$	max. 300	600	1200	V
Crest working reverse voltage	$V_{RWM}$	max. 200	400	800	V
Continuous reverse voltage	$V_R$	max. 200	400	800	V

Currents

## Average forward current (averaged

over any 20 ms period) up to  $T_{mb} = 115^{\circ}\text{C}$   
at  $T_{mb} = 125^{\circ}\text{C}$

$I_{F(AV)}$  max. 12 A  
 $I_{F(AV)}$  max. 10 A

R.M.S. forward current

 $I_{F(RMS)}$  max. 20 A

Repetitive peak forward current

 $I_{FRM}$  max. 60 A

Non-repetitive peak forward current

( $t = 10$  ms; half sine-wave)  $T_j = 175^{\circ}\text{C}$  prior to surge;  
with reapplied  $V_{RWMmax}$

 $I_{FSM}$  max. 125 ATemperatures

Storage temperature

 $T_{stg}$  -55 to +175  $^{\circ}\text{C}$ 

Junction temperature

 $T_j$  max. 175  $^{\circ}\text{C}$ 

## THERMAL RESISTANCE

From junction to ambient in free air

 $R_{th j-a}$  = 50  $^{\circ}\text{C/W}$ 

From junction to mounting base

 $R_{th j-mb}$  = 3  $^{\circ}\text{C/W}$ 

From mounting base to heatsink

 $R_{th mb-h}$  = 0,5  $^{\circ}\text{C/W}$ 

## CHARACTERISTICS

Forward voltage at  $I_F = 15$  A;  $T_j = 25^{\circ}\text{C}$  $V_F$  < 1,4 V <sup>1)</sup>Reverse current at  $V_R = V_{RWMmax}$ ;  $T_j = 125^{\circ}\text{C}$  $I_R$  < 200  $\mu\text{A}$ 

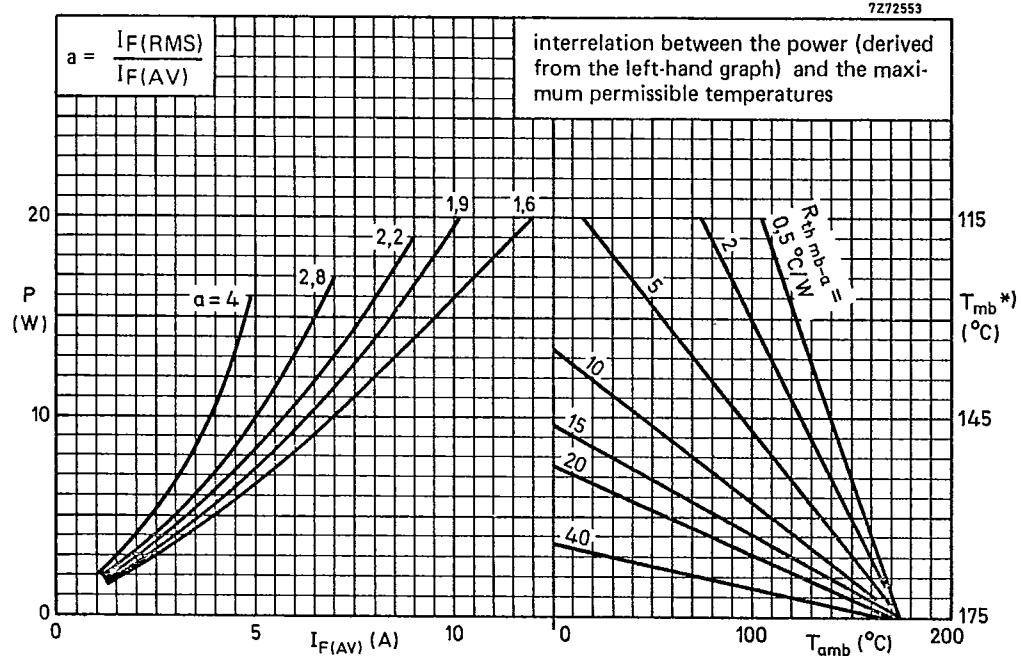
## MOUNTING INSTRUCTIONS

The top connector should neither be bent nor twisted; it should be soldered into the circuit so that there is no strain on it.

During soldering the heat conduction to the junction should be kept to a minimum.

1) Measured under pulse conditions to avoid excessive dissipation.

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\*)  $T_{mb}$ -scale is for comparison purposes only and is correct only for  $R_{th\ mb-a} \leq 22\ ^{\circ}\text{C}/\text{W}$

